1765

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

KIYOKU, HIROYUKI, et al.

Application No.: 09/986,332

Confirmation No.: 5542

Filed: November 8, 2001

Docket No: Q66212

Group Art Unit: 1765

Examiner: Anderson, Matthew A.

#10
6/26/03
MW

For: NITRIDE SEMICONDUCTOR GROWTH METHOD, NITRIDE SEMICONDUCTOR SUBSTRATE, AND NITRIDE SEMICONDUCTOR DEVICE

AMENDMENT UNDER 37 C.F.R. § 1.111

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

In response to the Office Action dated December 19, 2002, please amend the above-identified application as follows:

IN THE CLAIMS:

Please cancel claims 2-4, 6, 8-12, 16, 17, 23, 25, and 189-197 without prejudice or disclaimer.

Please enter the following amended claims:

1. (Amended) A nitride semiconductor growth method comprising the steps of:

(a) forming a first selective growth mask on a support member made up of a dissimilar substrate made of a material different from a nitride semiconductor and having a major surface forming a $(11\bar{2}0)$ plane, and an underlayer made of a nitride semiconductor formed on the major surface of the dissimilar substrate, said first selective growth mask having a plurality of first windows selectively exposing an upper surface of the underlayer of the support member; and